

Absolute Maximum Ratings (@TA = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	200	V
Collector-Emitter Voltage	$V_{\sf CEO}$	150	V
Emitter-Base Voltage	V_{EBO}	7	V
Continuous Collector Current	Ic	1	Α
Peak Pulse Current	Ісм	3	Α
Base Current	Ι _Β	500	mA

Thermal Characteristics ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
	(Note 6)		1		
Power Dissipation	(Note 7)	P_{D}	1.5	W	
	(Note 8)		2.0		
	(Note 6)		125		
Thermal Resistance, Junction to Ambient Air	(Note 7)	$R_{\theta JA}$	83	°C/W	
	(Note 8)		60	1	
Thermal Resistance, Junction to Lead	(Note 9)	R _{θJL}	13	°C/W	
Operating and Storage Temperature Range		T_J,T_STG	-55 to +150	°C	

ESD Ratings (Note 10)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

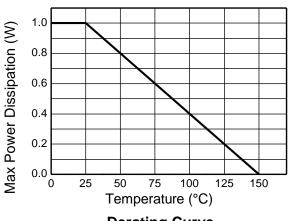
- 6. For a device mounted with the exposed collector pad on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
 7. Same as Note 6, except the device is mounted on 25mm x 25mm 1oz copper.
 8. Same as Note 6, except the device is mounted on 50mm x 50mm 1oz copper.
 9. Thereal exists 6, effort instance is related to 10 mm x 50mm 1oz copper.

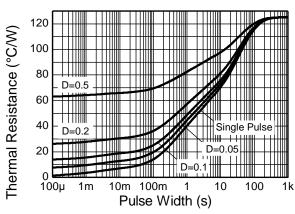
- Thermal resistance from junction to solder-point (on the exposed collector pad).
 Refer to JEDEC specification JESD22-A114 and JESD22-A115.





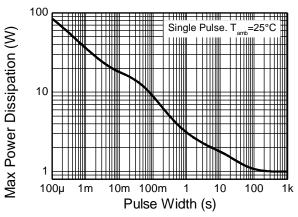
Thermal Characteristics and Derating Information



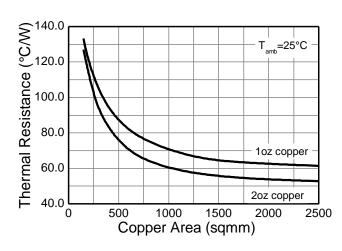


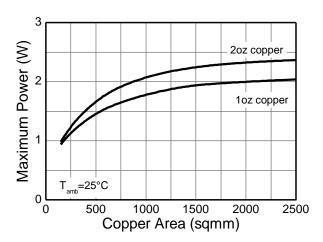
Derating Curve

Transient Thermal Impedance



Pulse Power Dissipation





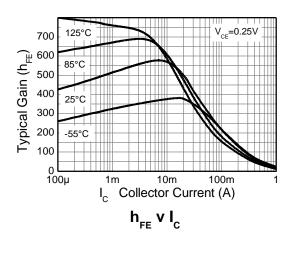


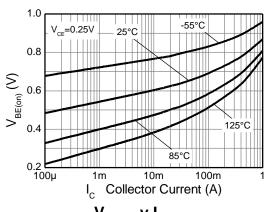
Electrical Characteristics (@T_A = +25°C unless otherwise specified.)

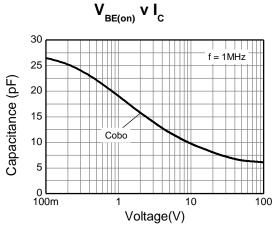
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
Collector-Emitter Breakdown Voltage (Note 11)	BV _{CEO}	150	175	-	V	I _C = 10mA	
Collector-Base Breakdown Voltage	BV _{CBO}	200	310	-	V	I _C = 100μA	
Collector Cut-Off Current	I _{CBO}	-	<1	50	nA	V _{CB} = 150V	
Collector Cut-Off Current	I _{CES}	-	<1	50	nA	V _{CE} = 150V	
Emitter Cut-Off Current	I _{EBO}	-	<1	50	nA	V _{EB} = 7V	
Static Forward Current Transfer Ratio (Note 11)	b	200 60	-	-		$I_C = 30$ mA, $V_{CE} = 5$ V $I_C = 85$ mA, $V_{CE} = 0.20$ V	
Static Forward Current Harister Ratio (Note 11)	h _{FE}	100	-	-	-	$I_C = 85 \text{ mA}, V_{CE} = 0.20 \text{ V}$ $I_C = 150 \text{ mA}, V_{CE} = 0.25 \text{ V}$	
Base-Emitter Turn-On Voltage (Note 11)	$V_{BE(on)}$	-	0.71	0.95	V	$I_C = 150 \text{mA}, V_{CE} = 0.25 \text{V}$	
Collector-Emitter Saturation Voltage (Note 11)	V _{CE(sat)}	-	-	0.25	V	$I_C = 100 \text{mA}, I_B = 5 \text{mA}$	
Delay Time	t _(d)	-	512	-	ns		
Rise Time	t _(r)	-	426	-	ns	$V_{CC} = 120V, I_C = 150mA,$	
Storage Time	t _(s)	-	3413	-	ns	$-I_{B2} = 1.5$ mA, $V_{CE}(ON) = 0.25$ V	
Fall Time	t _(f)	-	321	-	ns		
Storage Time	t _(s)	-	65	-	ns	$V_{CC} = 120V, I_C = 150mA,$	
Fall Time	t _(f)	-	294	-	ns	$-I_{B2} = 1.5 \text{mA}, V_{CE(ON)} = 4 \text{V}$	

Note: 11. Measured under pulsed conditions. Pulse width ≤ 300µs. Duty cycle ≤ 2%.

Electrical Characteristics (@T_A = +25°C unless otherwise specified.)





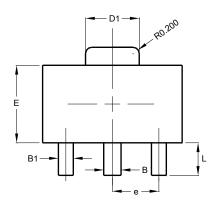


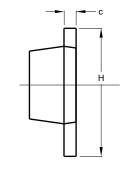
Capacitance v Voltage

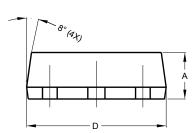


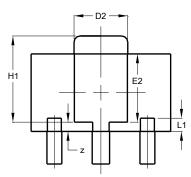
Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.





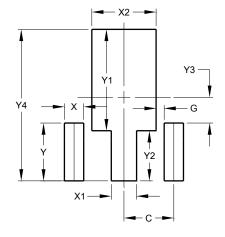




SOT89					
Dim	Min	Max	Тур		
Α	1.40	1.60	1.50		
В	0.50	0.62	0.56		
B1	0.42	0.54	0.48		
C	0.35	0.43	0.38		
D	4.40	4.60	4.50		
D1	1.62	1.83	1.733		
D2	1.61	1.81	1.71		
Е	2.40	2.60	2.50		
E2	2.05	2.35	2.20		
e	1	-	1.50		
Н	3.95	4.25	4.10		
H1	2.63	2.93	2.78		
L	0.90	1.20	1.05		
L1	0.327	0.527	0.427		
Z	0.20	0.40	0.30		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	value		
Dimensions	(in mm)		
С	1.500		
G	0.244		
X	0.580		
X1	0.760		
X2	1.933		
Υ	1.730		
Y1	3.030		
Y2	1.500		
Y3	0.770		
Y4	4.530		

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.





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